

IRF2204SPbF

IRF2204LPbF

HEXFET® Power MOSFET

Typical Applications

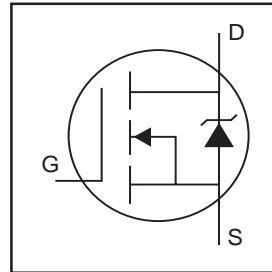
- Electric Power Steering
- 14 Volts Automotive Electrical Systems
- Lead-Free

Features

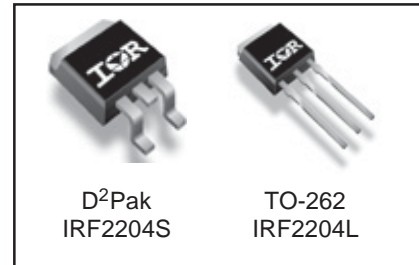
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features to this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



$V_{DSS} = 40V$
$R_{DS(on)} = 3.6m\Omega$
$I_D = 170A^{\textcircled{C}}$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	170 [Ⓒ]	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	120 [Ⓒ]	
I_{DM}	Pulsed Drain Current [Ⓓ]	850	
$P_D @ T_C = 25^{\circ}C$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy [Ⓔ]	460	mJ
I_{AR}	Avalanche Current [Ⓓ]	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy [Ⓔ]		mJ
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

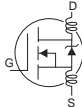
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	40	

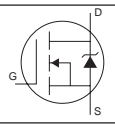
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International
IR Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.041	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	3.0	3.6	mΩ	V _{GS} = 10V, I _D = 130A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = 10V, I _D = 250μA
g _{fs}	Forward Transconductance	120	—	—	S	V _{DS} = 10V, I _D = 130A
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 40V, V _{GS} = 0V
		—	—	250		V _{DS} = 32V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -20V
Q _g	Total Gate Charge	—	130	200	nC	I _D = 130A
Q _{gs}	Gate-to-Source Charge	—	35	52		V _{DS} = 32V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	39	59		V _{GS} = 10V ④
t _{d(on)}	Turn-On Delay Time	—	15	—	ns	V _{DD} = 20V
t _r	Rise Time	—	140	—		I _D = 130A
t _{d(off)}	Turn-Off Delay Time	—	62	—		R _G = 2.5Ω
t _f	Fall Time	—	110	—		V _{GS} = 10V ④
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	5890	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1570	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz, See Fig. 5
C _{oss}	Output Capacitance	—	8000	—		V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz
C _{oss}	Output Capacitance	—	1370	—		V _{GS} = 0V, V _{DS} = 32V, f = 1.0MHz
C _{oss eff.}	Effective Output Capacitance ④	—	2380	—		V _{GS} = 0V, V _{DS} = 0V to 32V

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	170⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	850		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 130A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	68	100	ns	T _J = 25°C, I _F = 130A
Q _{rr}	Reverse Recovery Charge	—	120	180	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

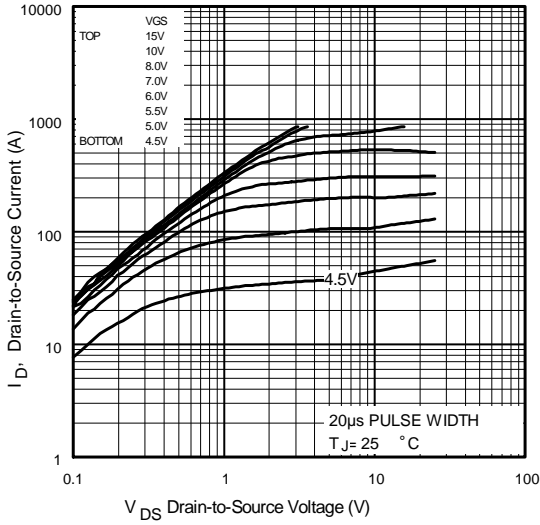


Fig 1. Typical Output Characteristics

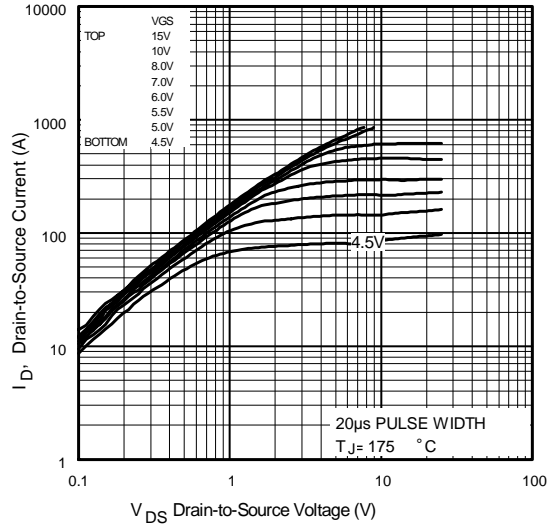


Fig 2. Typical Output Characteristics

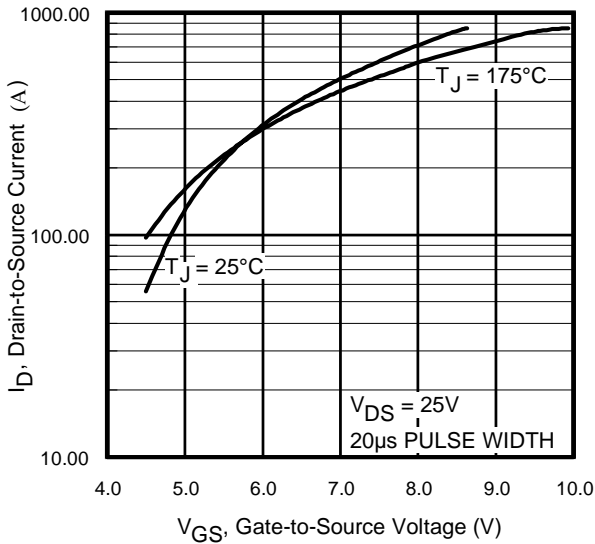


Fig 3. Typical Transfer Characteristics

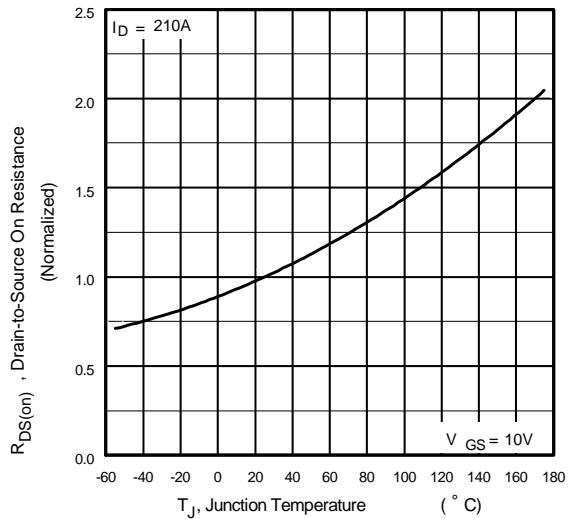


Fig 4. Normalized On-Resistance Vs. Temperature

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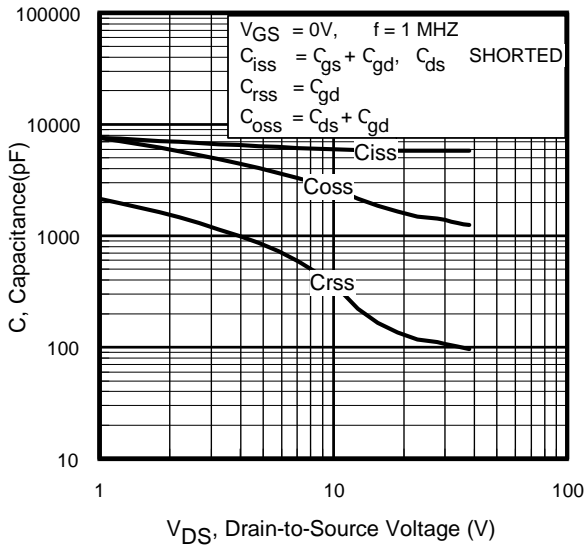


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

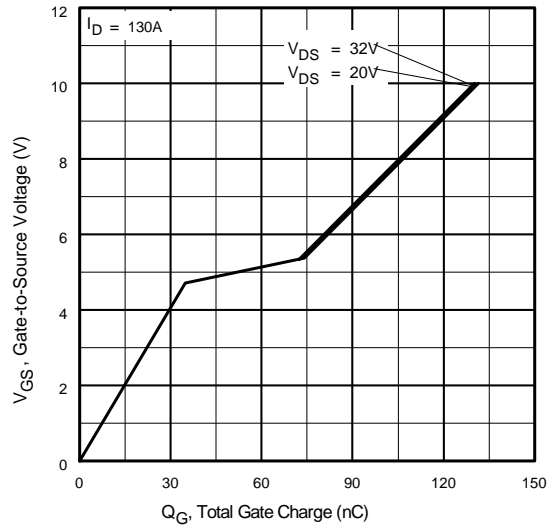


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

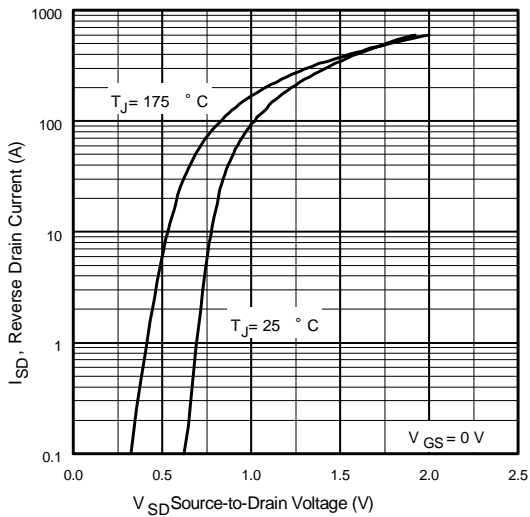


Fig 7. Typical Source-Drain Diode Forward Voltage

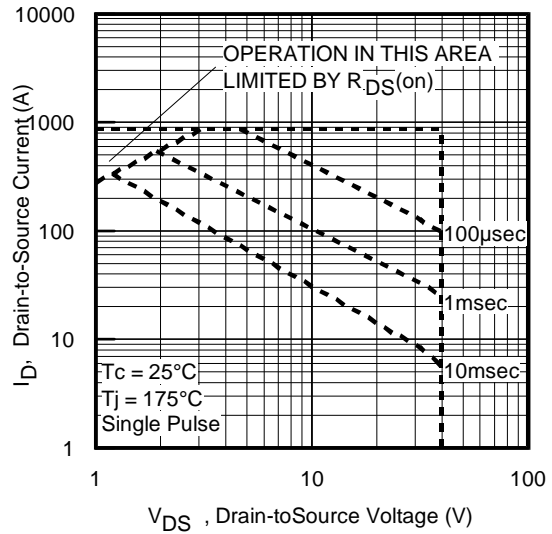


Fig 8. Maximum Safe Operating Area

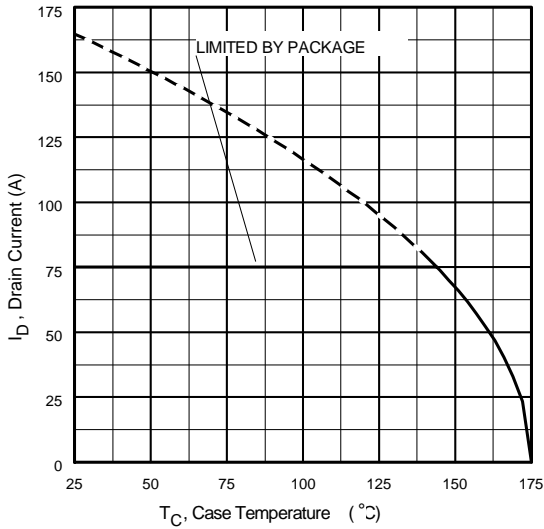


Fig 9. Maximum Drain Current Vs. Case Temperature

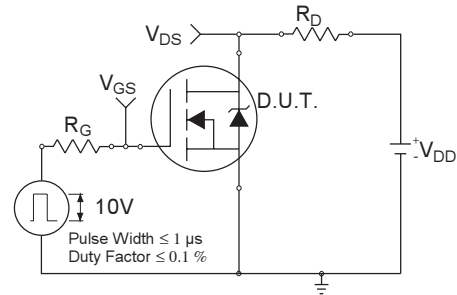


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

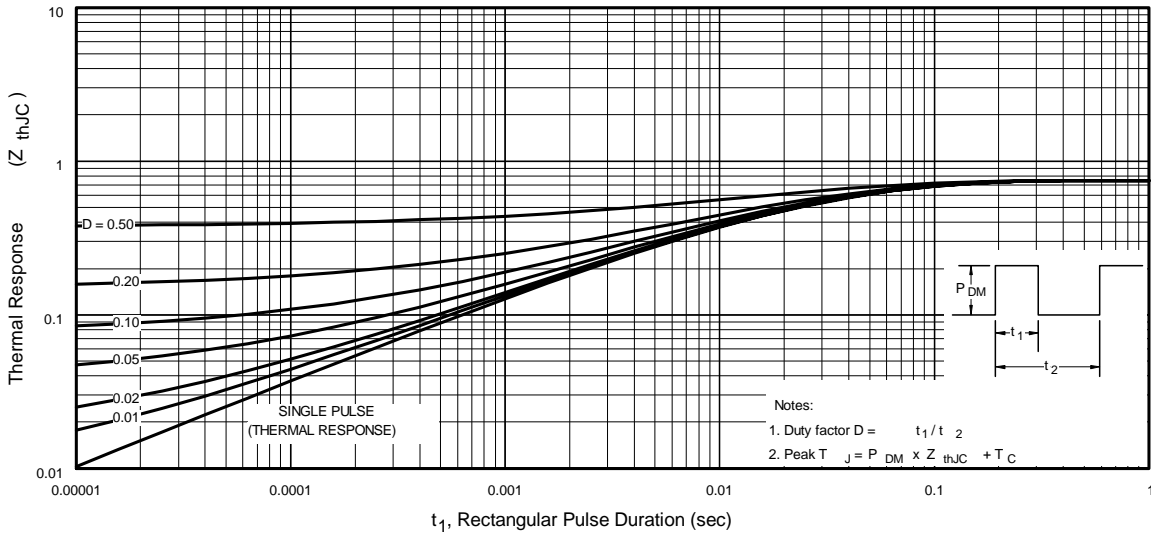


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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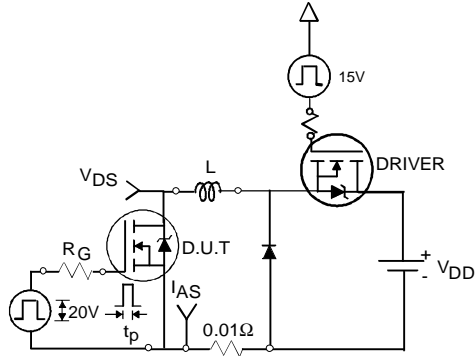


Fig 12a. Unclamped Inductive Test Circuit

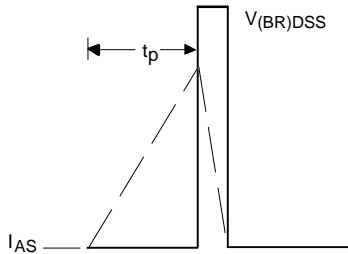


Fig 12b. Unclamped Inductive Waveforms

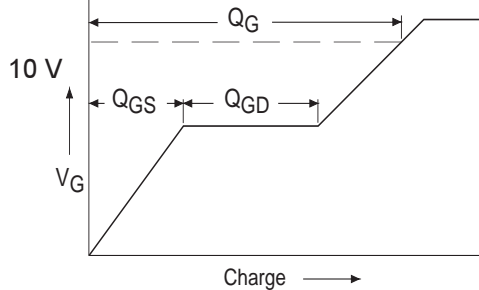


Fig 13a. Basic Gate Charge Waveform

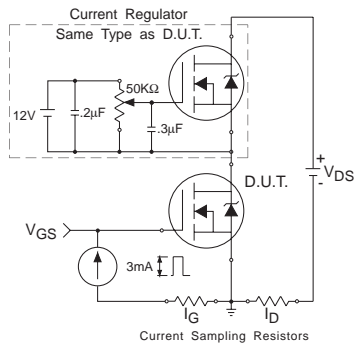


Fig 13b. Gate Charge Test Circuit

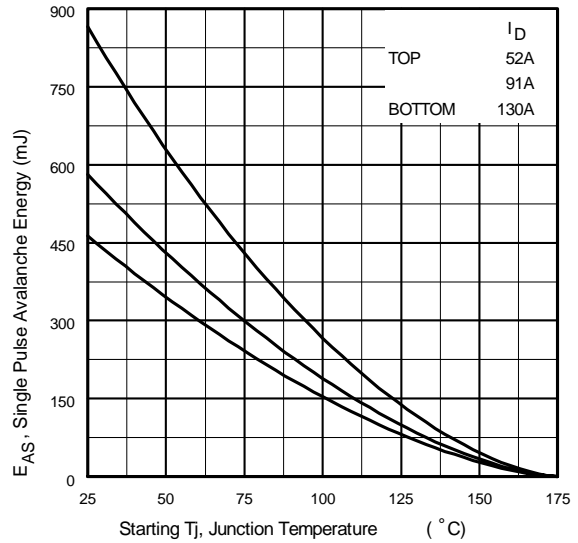


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

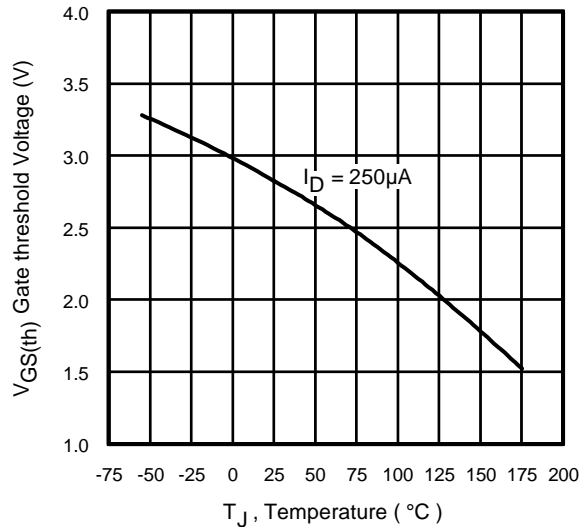


Fig 14. Threshold Voltage Vs. Temperature

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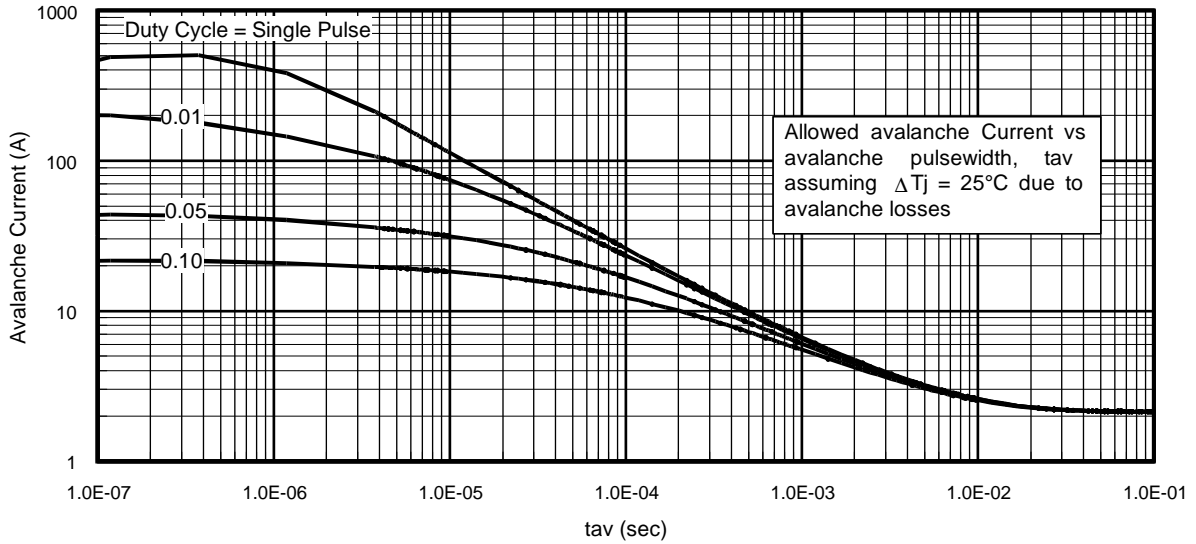


Fig 15. Typical Avalanche Current Vs.Pulsewidth

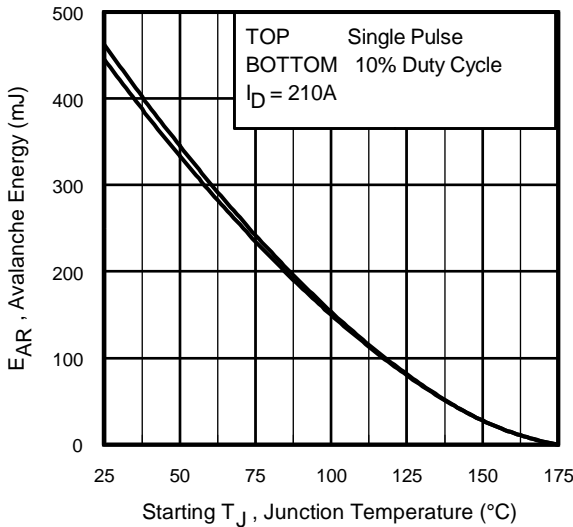


Fig 16. Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)**

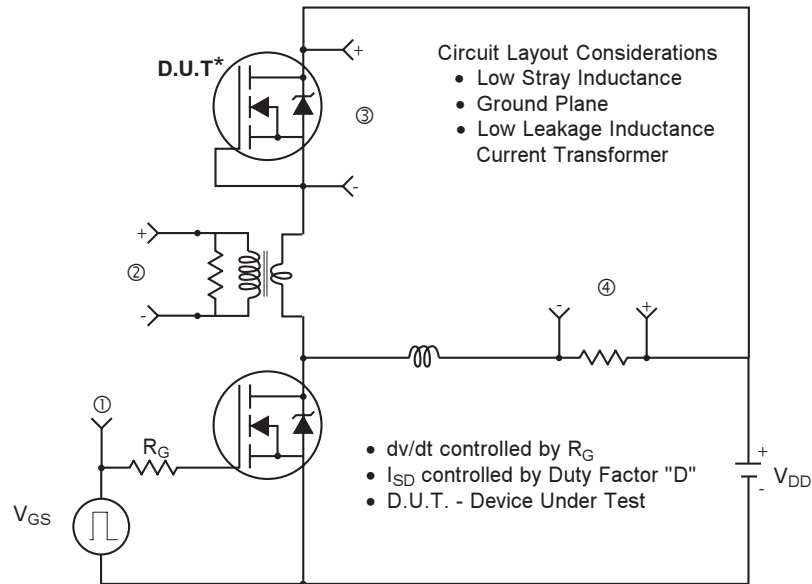
1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

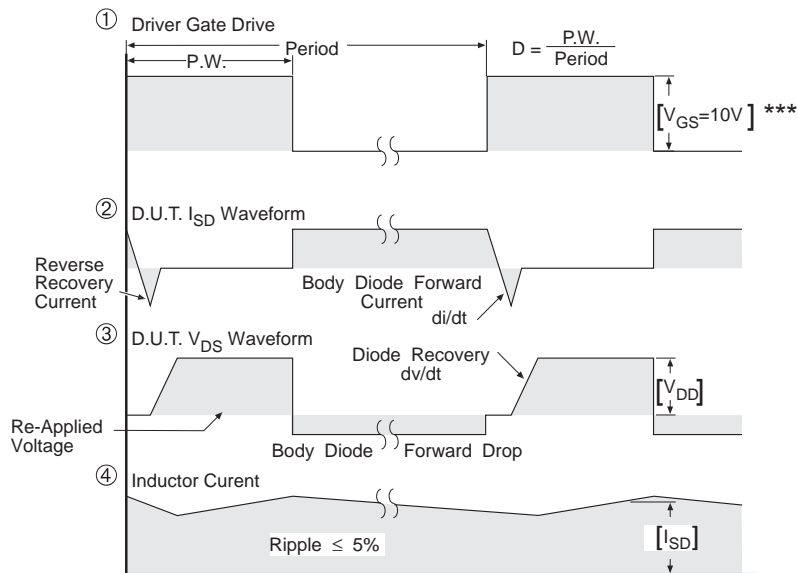
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel

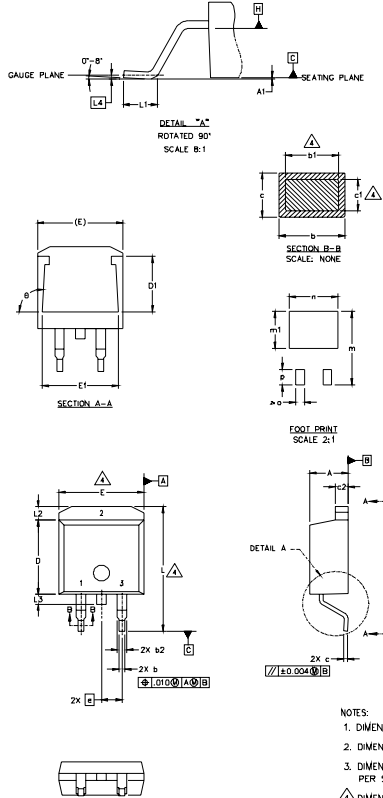


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 17. For N-channel HEXFET® power MOSFETs

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	4
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEM-FET	IGBTs, CoPACK	DIODES
1 - GATE	1 - GATE	1 - ANODE *
2 - DRAIN	2 - COLLECTOR	2 - CATHODE
3 - SOURCE	3 - EMITTER	3 - ANODE

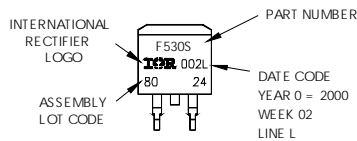
* PART DEPENDENT.

NOTES:

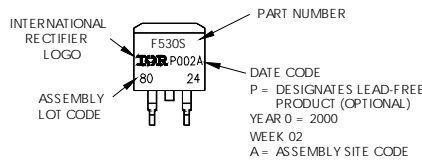
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON VW02, 2000
IN THE ASSEMBLY LINE "L"
Note: "P" in assembly line
position indicates "Lead-Free"



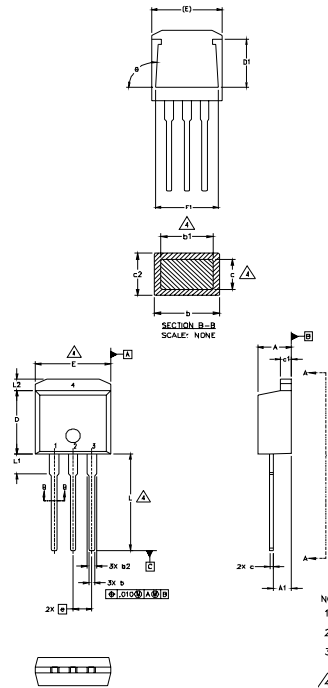
OR



IRF2204S/LPbF

TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

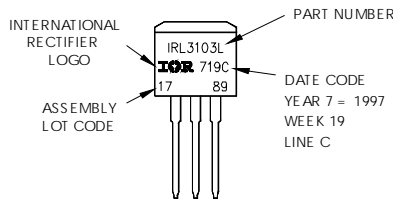
HEXFET	IGBT
1.- GATE	1 - GATE
2.- DRAIN	2 - COLLECTOR
3.- SOURCE	3 - EMITTER
4.- DRAIN	

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

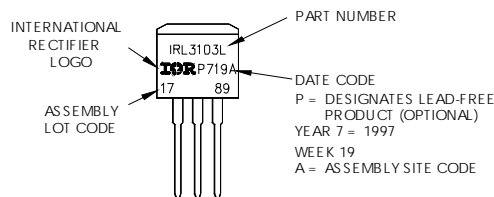
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

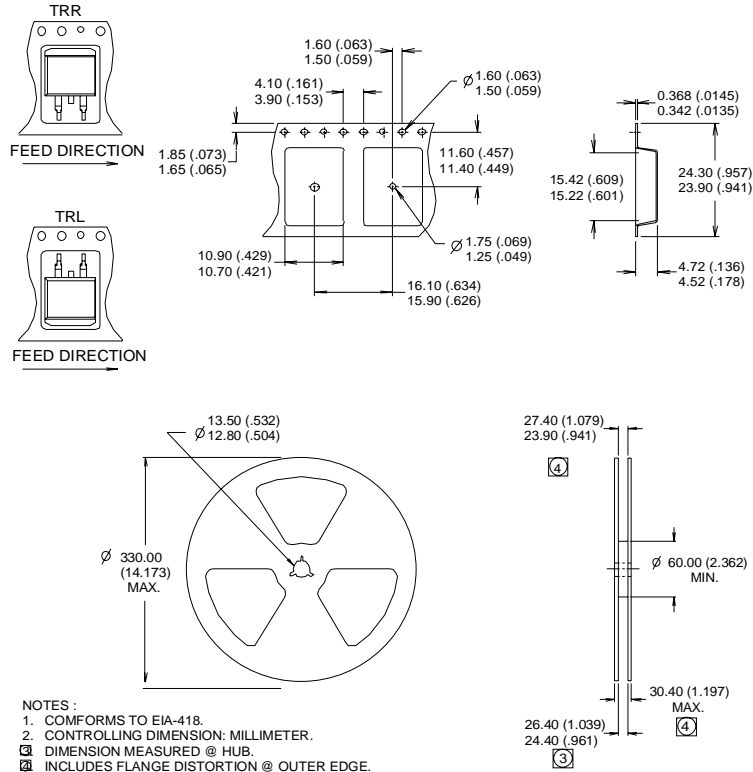


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.06\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 130\text{A}$. (See Figure 12).
- ③ $I_{SD} \leq 130\text{A}$, $di/dt \leq 170\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑦ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site,

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.06/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>